

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph on page 13 starting on line 6 with the following paragraph:

The embodiment of process according to the present invention then continues with replacing film 301 bonded to carrier 320 on a layer 350 of transistors 352 of a third substrate 360 shown in **Figure 11**. Transistors 352 and 316 are interconnected by lines 354. The new assembly illustrated in **Figure 11** is then heated at a temperature of 400 degrees Celsius at which the film 301 bonds to the film 350 and the carrier 320 debonds from the film 301 of transistors 316.